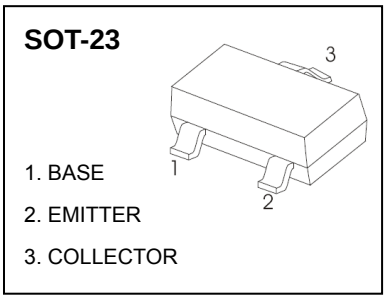
S8550

SOT-23 Plastic-Encapsulate Transistors

TRANSISTOR (PNP)



FEATURES

- **Complimentary to S8050**
- **Collector current: I_C=0.5A**

MARKING : 2TY

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

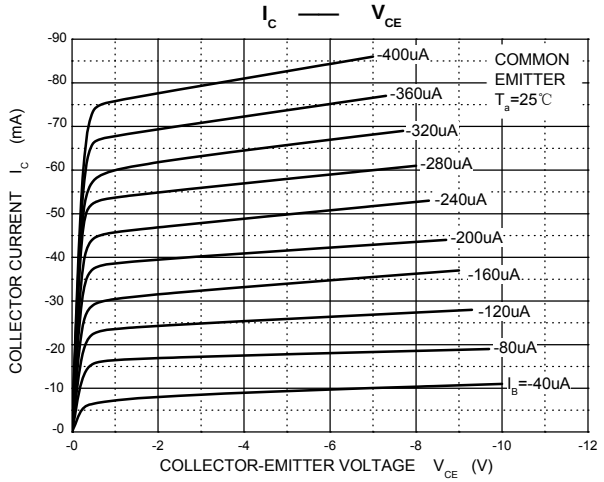
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

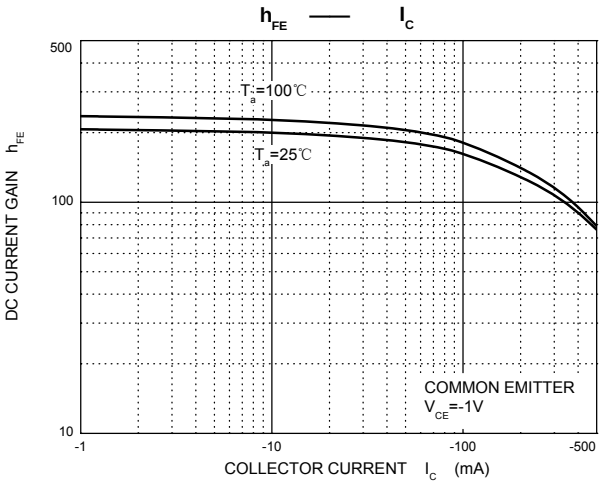
Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = -100μA, I_E=0	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C =-1mA, I_B=0	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5		V
Collector cut-off current	I_{CBO}	V_{CB}= -40V, I_E=0		-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}= -20V, I_B=0		-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -3V, I_C=0		-0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}= -1V, I_C= -50mA	120	400	
	$h_{FE(2)}$	V_{CE}= -1V, I_C= -500mA	50		
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA, I_B= -50mA		-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA, I_B= -50mA		-1.2	V
Transition frequency	f_T	V_{CE}= -6V, I_C= -20mA f=30MHz	150		MHz

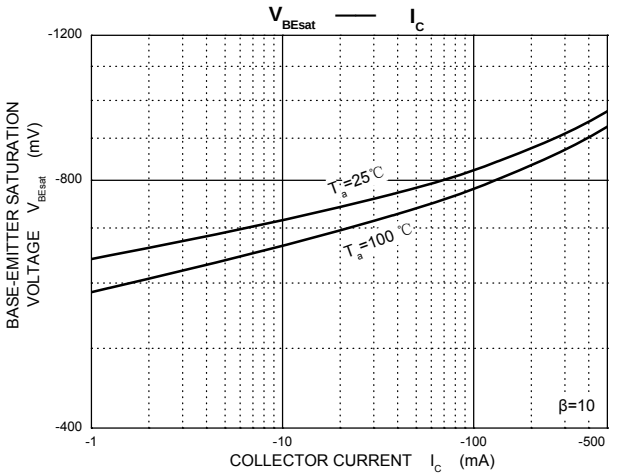
CLASSIFICATION OF $h_{FE(1)}$

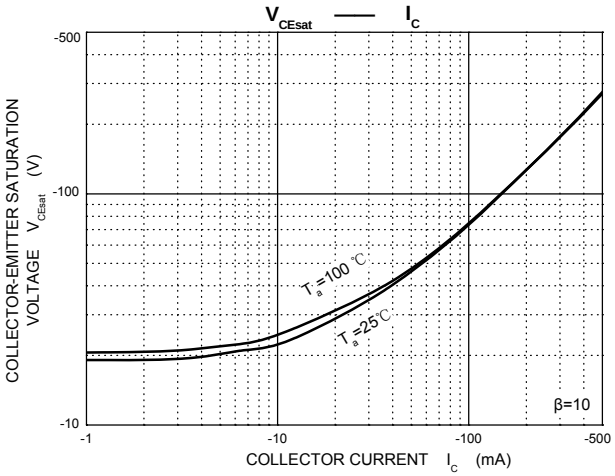
Rank	L	H	J
Range	120-200	200-350	300-400

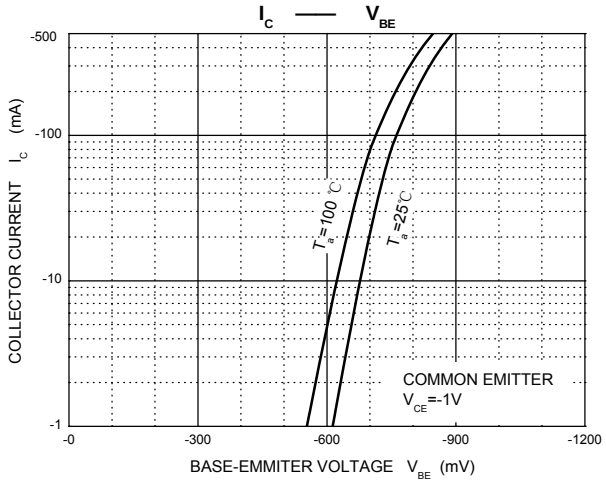
Typical Characteristics

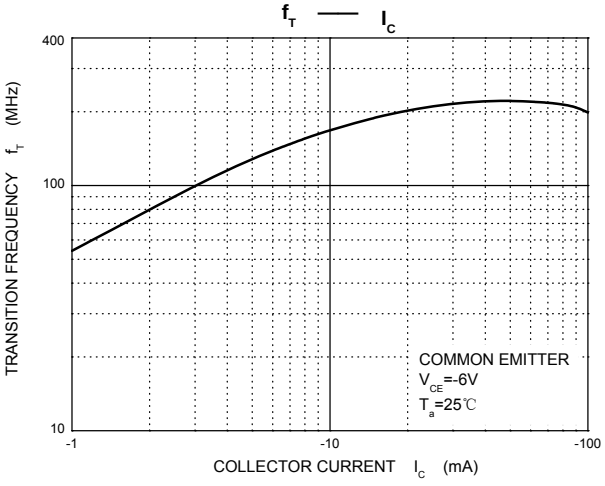


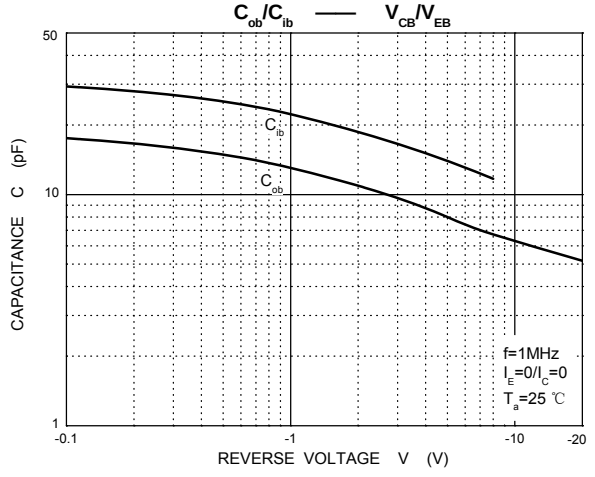


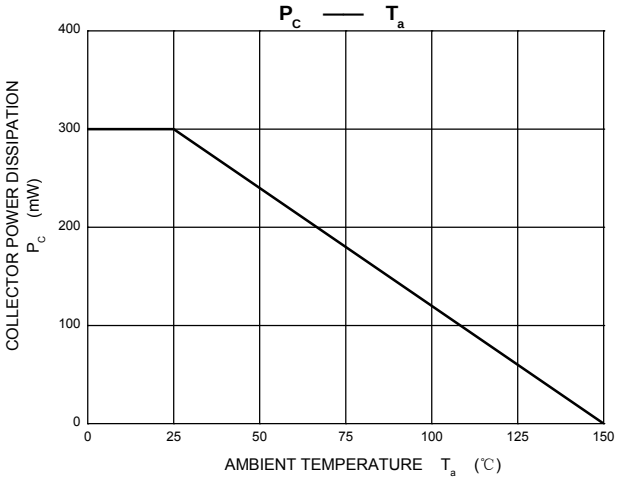












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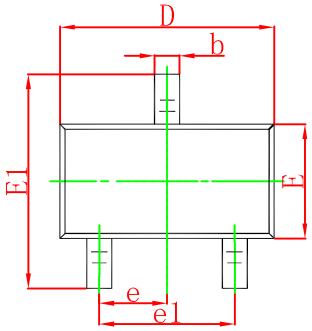
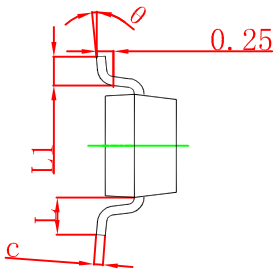
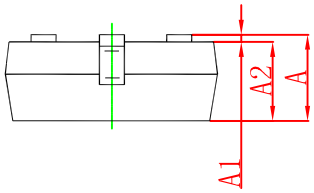
SOT-23 Package Outline Dimensions

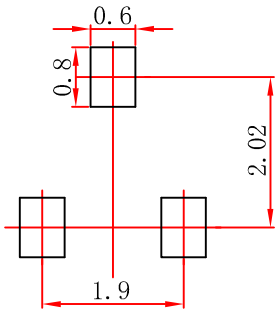






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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